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(54) **METHOD FOR DEPOSITING PHOSPHORUS  
CONTAINING SILICON LAYER**

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**ABSTRACT**

A method for epitaxially growing a phosphorus doped silicon layer on a substrate is disclosed. Embodiments of the presently described method comprise exposing a substrate to a silicon precursor and to a phosphorus precursor, wherein the exposure of the substrate to the phosphorus precursor is done during an overlapping period with the exposure to the silicon precursor.

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